AMENDMENTS TO THE CLAIMS:

Please amend the claims as detailed herein.

1. (Currently Amended) A method of imaging the semiconductor sites in an integrated circuit (IC), comprising the steps of:

setting-up a device that simultaneously produces two separate images of the ICa sample of said IC from one light source; and

refining the said images to generate an exclusive high-contrast image of the said semiconductor sites.

- 2. (Currently amended) The method of claim 1, wherein said method generates an exclusive high-contrast image of the metallic sites in anthe IC sample.
- 3. (Currently amended) The method of claim 1, wherein said device is comprised of of comprises:

an optical microscope set-up;

a light source that excites the IC sample;

a beam-scanning and sample-scanning mechanism to control thea focused excitation beam and transverse and axial scanning of the IC sample;

a driving and control software to scan the said focused excitation beam from one pixel location of the <u>IC</u> sample to another;

a personal computer (PC) to implement the control of the instrumentsaid optical microscope and said beam-scanning mechanism, thea data acquisition system and the post-detection processing, awherein said data acquisition system consisting of includes two analog-to-digital converters to digitize thea photodetector signal and thea 1P-OBIC signal in the said PC;

a data control software whichthat allows the said PC to control the said scanning of the said focused beam on the IC sample and to acquire the a resulting confocal reflectance signal and 1P-OBIC signals that are generated from the IC sample; and a photodetector to convert the said confocal reflectance signal from the IC sample

into an equivalent electrical signal whichthat is sampled by the said analog-to-digital converters to the said PC.

- 4. (Currently amended) The method of claim 3, wherein said microscope is a beam-scanning confocal reflectance microscope that simultaneously generates both <u>a</u> one-photon optical beam-induced current (1P-OBIC) image and <u>a</u> confocal reflectance image of the IC sample.
- 5. (Currently amended) The method of claim 3, wherein said light source is selected from the group consisting of a laser and a spectrally filtered light source with a broadband spectrum.

6. (Cancelled)

- 7. (Currently amended) The method of claims 5-and 6, wherein said device includes via a beam splitter, the output beam of the light source is directed to a scanning mirror system composed of having two galvanometer mirrors for x and y scanning, and two lenses that constitute a 4f transfer lens, wherein said light source has an output beam that is directed to said scanning mirror system via a beam splitter.
- 8. (Currently amended) The method of claim 7, wherein <u>said device includes</u> another pair of lenses <u>that</u> expands and collimates <u>thesaid</u> scanned <u>output</u> beam and inputs itsaid scanned output beam to an optical microscope assembly.
- 9. (Currently amended) The method of claim 8, wherein <u>said device includes</u> an Infinity-corrected objective lens <u>that</u> focuses <u>thesaid</u> beam into <u>thean</u> exposed top surface of <u>thesaid</u> integrated circuit.
- 10. (Currently amended) The method of claim 9, wherein <u>said device includes</u> a <u>pair of digital-to-analog converters to achieve</u> precise two-dimensional scan control of <u>thesaid</u> focused beam is achieved via a pair of digital to analog converters.

- 11. (Currently amended) The method of claim 10, wherein the said device provides reflected light that is collected back by the said Infinity-corrected objective lens and focused by a lens towards a pinhole that is placed in front of said photodetector.
- 12. (Currently amended) The method of claim 11, wherein the said 1P-OBIC is measured by inputting the an output of the said pinhole that is nearest to the a probe surface area to a current-to-voltage converter composed of an operational amplifier and a feedback resistor.
- 13. (Currently amended) The method of claim 12, wherein the said device includes another converter input that is thea common reference for the electronic circuits including the integrated circuit sample.
- 14. (Currently amended) The method of claim 1, wherein the <u>said</u> exclusive high-contrast image of the <u>said</u> semiconductor site is derived from the <u>a</u> pixel to pixel product of the <u>an</u> IP-OBIC image and the <u>a</u> confocal reflectance image using the <u>an</u> equation $s(x,y,z)=i_f(x,y,z)i_s(x,y)$ where $s(x,y,z)\geq 0$.
- 15. (Currently amended) The method of claim 2, wherein ansaid exclusive high-contrast image of the said metallic sites is obtained from the a product of the a complementary OBIC image and the a confocal image using the an equation: $m(x,y,z)=i_r(x,y,z)i_m(x,y)$ where $i_m(x,y)=\kappa-i_s(x,y)$ and κ is a constant that represents the a highest s(x,y,z) value that is possible for a given optical set-up.